

# Characterization of Zn-Doped CdO Nanoparticles Thin Films Synthesized by Pulsed Laser Deposition

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# ARTICLEINFOABSTRACTArticle History:<br/>Accepted: 05 May 2023<br/>Published: 22 May 2023In this investigation, thin films of CdO:Zn were synthesized by using the<br/>technology of pulsed lasers. Additionally, the effect of different<br/>concentrations of Zn doping on the material's physical properties was<br/>investigated. According to XRD research, the films have a polycrystalline<br/>etructure, and it was discovered that the size of the grantallities changes

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Keywords: CdO; PLD; XRD; band gap; Hall effects

# I. INTRODUCTION

Due to its narrow band gap (2.2–2.7eV), n-type conductivity, and good transparency in the near-infrared spectrum, as well as its favorable electrochemical properties, Cadmium Oxide (CdO) is well known as one of the preferred II–IV compound metal oxide semiconductors in a wide range of applications [1-3In addition, CdO thin films have found use in a wide variety of applications, such as gas sensors [4], antibacterial agents [5], heterojunction diodes [6], translucent conducting oxide [7], nonlinear

optical devices [8] and solar cells [9]. [4-9] CdO thin films were made using various techniques such chemical bath deposition (CBD) [10], successive ionic layer reaction andadsorption [11], magnetron sputtering [12], physical vapor deposition (PVD) [13], deposition by pulsed laser [14], spin coating [15], chemical spray method [16], and atmosphericpressure chemical vapor deposition (APCVD) [17]. In the work that we are doing, we are going to investigate how the structural, morphological, optical, and electrical properties of Zn-doped CdO thin films are affected by the concentration of Zn doping (0, 1, 3,

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and 5%), and we will do this using the pulsed laser methodology.

#### II. EXPERIMENTAL

On BK7 glass and silicon substrates, thin CdO:Zn films with doping concentrations of 0%, 1%, 3%, and 5% were deposited using a procedure that involved the use of a pulsed laser. Both the CdO and the Zn granules that were utilized came from Sigma-Aldrich and had a purity level of 99.9%. For the purpose of fabricating thin coatings, CdO:Zn pellets of varying doping concentrations were utilized. These pellets were then subjected to a vacuum pressure of 10-5 mbar. The laser had an energy of 200 mJ, and there were 200 separate blasts. In addition, the substrate was heated to a temperature of 300 degrees Celsius, and the distance from the objective to the substrate was five centimeters. Reflectometer measurements were used to determine the thickness of CdO:Zn thin layers, which came out to be 150.4 nanometers on average.

#### **III.RESULTS AND DISCUSSION**

X-ray diffratometer was used to examine the structural characteristics. Figure 1 depicts the diffraction spectra for CdO:Zn thin films. All films are polycrystalline CdO with a favored orientation along (111). There are no apparent concentrations of zinc metal or zinc oxide. The typical crystallite size of CdO:Zn thin films has been calculated using Sherrer's equation [18]:

$$D_A = \frac{0.94\lambda}{\beta \cos\theta}(1)$$

Where  $D_A$ ,  $\lambda$ ,  $\beta$ , and  $\theta$  are the size of ,thewavelength of X-ray is about (1.54056 Å), the full width at half maxima, and the Bragg's angle, respectively. The average crystallite size was found to vary with Zn doping concentrations, the calculated values were tabulated in table 1. The microstrain  $\varepsilon$  of CdO:Znthin films has been estimated by the following formula [19]:

$$\varepsilon = \frac{\beta}{4\tan\theta} \left(2\right)$$

The calculated values of microstrain are listed in table 1.

Table 1 the average size of crystallite and microstrai	n
of CdO:Zn thin films.	

Sample	Average Crystallite	Micro Strain
	size D <sub>A</sub> (nm)	$\epsilon \times 10^{\text{-3}}$
CdO pure	23	4.97
CdO:Zn1%	40	1.97
CdO:Zn3%	36	3.07
CdO:Zn5%	26	4.07



Fig.1 XRDpatterns CdO:Zn thin films

The morphology of thin layers made of CdO:Zn was examined using scanning electron microscopy. As can be seen in Figure 2, none of the films contain any voids or fractures; additionally, one can plainly make out spherical nanoparticles distributed along the



surface of thin films. In addition, the concentrations of Zn doping have been shown to cause changes in the diameters of these particles.



Fig.2 FESEM micrographs of a) pure CdO, b) CdO:Zn 1% , c) CdO:Zn 3%, and d) CdO:Zn 5%

The UV-Vis-NIR spectrophotometer was used to examine the optical characteristics of CdO:Zn thin films at wavelengths between 300 and 1100 nm.The transmittance the CdO:Znthin spectra of filmswereshown in fig.3, the transmittancespectrahave the same manner with increasing wavelength. Moreover CdO:Zn5% filmshave the highest transmittance about65% in the NIR region due to the minimal scattering radiation occurred on the surface of nanoparticles. The following equation [20] was used to calculate the absorption coefficient:

$$\alpha = -\frac{1}{x} \ln (T)(3)$$

Where  $\alpha$  is absorption coefficient, *x*, and *T* are film thickness and transmittance of the films.



Fig.3trasmittance spectra of CdO:Zn thin films

Absorption coefficientsforCdO:Znfilmswere found to decrease with increasing wavelengthas shown in fig.4. Further,  $\alpha$  was found to vary with Zn doping concentrations and have high values ( $\alpha \ge 10^6$ ) m<sup>-1</sup> for all films.



Fig.4 the absorption coefficients of CdO:Znthin films

The energy gap for CdO:Zn thin films was estimated using the following equation [21]:

$$(\alpha h \upsilon)^2 = B(h \upsilon - E_g) \tag{4}$$

Where *B* is a constant, *h* $\cup$  and *Eg* are the photon energy and energy gap. According to Fig. 5, the energy gaps increased from 2.525 eV for pure CdO to 2.747 eV, 2.673 eV, and 2.851 eV, respectively, for CdO:Zn1%, CdO:Zn3%, and CdO:Zn5% thin films.Compared to bulk CdO, the calculated values of the energy gap were higher, this might attributed to the size



reduction in the nanoparticles, this findings are coincident with the work reported in ref. [22].



Hall effect measurements were employed to assess the electrical properties of CdO:Zn thin films in a Van Der Pauw configuration.Hall effectcharecterestics were tabulated in table 2, according to this measurements, all films have n-type conductivity. Moreover the highest conductivity and mobility arerecored in CdO:Zn1% thin films.

	Shoot	Corrior	Hall		Mob	
Sampl	Desis	Carner	Coeff	Condu	ility	
	Kesis Concen	icient	ctivity	μ	Ту	
e	tance	tration	RH	σ (Ω	(cm <sup>2</sup>	pe
	Rs $n \times 10^{10}$	(cm-3	<b>cm)</b> -1	$V^{1}\text{s}^{\text{-}}$		
	(Ω)	(cm⁻³)	C-1)		<sup>1</sup> )	
CdO	120	1.96	2 26	367	121	ñ
pure	130	1.00	-3.30	502	0	11
CdO:	03.3	0.874	714	526	383	n
Zn1%	50.0	0.074	-7.14	550	0	11
CdO:	170	1 70	3 67	397	140	n
Zn3%	127	1.72	-3.02	507	0	11
CdO:	173	1.86	3 35	108	137	n
Zn5%	120	1.00	-0.05-	UU	0	11

Table 2 Hall effectcharacteristics of CdO:Zn thin films

## **IV.CONCLUSIONS**

To summarize, the pulsed laser technique was used to produce CdO:Zn thin films. Additionally, the influence of Zn concentrations on the morphological, structural, electrical ,optical properties of the films was investigated. The crystallite size was found to vary from (23) nm to (40) nm by Zn doping concentration, as well as the micro strain was effected. SEM analysis show the films comprised of nanoparticles with sizes (43-91) nm. XRD analysis reveals the polycrystalline structure of cubic CdO. It was found that the energy difference increased from (2.525) eV to (2.851) eV when the amount of Zn in the compound was raised. The Hall effect measurements show that all of the films have n-type conductivity, and the films found to have high electrical conductivities along with large concentrations of speed carriers. These characteristics give the films that have been prepared the ability to have a variety of numerous applications in subjects that span across multiple disciplines.

## V. REFERENCES

- [1]. Benhaliliba, M., et al. "Luminescence and physical properties of copper doped CdO derived nanostructures." Journal of Luminescence 132.10 (2012): 2653-2658.
- [2]. Dakhel, A. A. "Optical and electrical properties of copper-doped nano-crystallite CdO thin films." Solid state sciences 31 (2014): 1-7.
- [3]. Raj, I. Loyola Poul, et al. "A comprehensive study on effect of annealing on structural, morphological and optical properties of CdO and photodetection of heterojunction n-CdO/p-Si diode." Optik 241 (2021): 166406.
- [4]. Salunkhe, R. R., and C. D. Lokhande. "Effect of film thickness on liquefied petroleum gas (LPG) sensing properties of SILAR deposited CdO thin films." Sensors and Actuators B: Chemical 129.1 (2008): 345-351.

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- [5]. Gupta, Vinod Kumar, et al. "Zn doped CdO nanoparticles: structural, morphological, optical, photocatalytic and anti-bacterial properties." Journal of colloid and interface science 504 (2017): 164-170.
- [6]. Karataş, Şükrü, and FahrettinYakuphanoğlu. "Analysis of electronic parameters of nanostructure copper doped cadmium oxide/psilicon heterojunction." Journal of alloys and compounds 537 (2012): 6-11.
- [7]. Yahia, I. S., et al. "Optical properties of Al-CdOnano-clusters thin films." Superlattices and Microstructures 64 (2013): 178-184.
- [8]. Henari, F. Z., and A. A. Dakhel. "Linear and nonlinear optical properties of hydrogenated CdO thin films." Laser physics 18.12 (2008): 1557-1561.
- [9]. Murali, K. R., et al. "Sol-gel dip coated CdO: Al films." Journal of Alloys and Compounds 503.2 (2010): 350-353.
- [10].Ruvalcaba-Manzo, S. G., et al. "Study of optical, morphological, structural, and chemical properties of CdO thin films synthesized by thermal annealing transformation of CdCO3 thin films." Optical Materials 132 (2022): 112742.
- [11].Salunkhe, R. R., et al. "Structural, electrical and optical studies of SILAR deposited cadmium oxide thin films: annealing effect." Materials Research Bulletin 44.2 (2009): 364-368.
- [12].Abed, Husam R., Ameer I. Khudadad, and Ali A. Yousif. "Impact of high vacuum annealing temperature on the structural, photoluminescence, and room temperature liquefied petroleum gas sensing of direct current magnetron sputtered CdO films." Materials Chemistry and Physics 289 (2022): 126446.
- [13].Dakhel, A. A. "Improving carriers mobility in copper and iron-codopedCdO." Materials science in semiconductor processing 17 (2014): 194-198.
- [14].Al-Dujayli, S. M. A., and N. A. Ali. "The effects of CuO doping on structural, electrical and optical properties of CdO thin films deposited by pulsed

laser deposition technique." JOURNAL OF OVONIC RESEARCH 18.4 (2022): 579-590.

- [15].Alahmed, Zayed A., et al. "Optical band gap controlling of nanostructure Mn doped CdO thin films prepared by sol-gel spin coating method." Optik 126.5 (2015): 575-577.
- [16].Ravikumar, M., et al. "Fabrication of Eu doped CdO [Al/Eu-nCdO/p-Si/Al] photodiodes by perfume atomizer based spray technique for opto-electronic applications." Journal of Molecular Structure 1160 (2018): 311-318.
- [17].Terasako, T., et al. "Structural and optical properties of CdO nanostructures prepared by atmospheric-pressure CVD." Thin Solid Films 528 (2013): 237-241.
- [18].Salih, Ammar T., et al. "Study of structural phase transition in nanocrystalline Cobalt Oxide thin films by pulsed laser deposition." Materials Research Express 6.7 (2019): 076415.
- [19].Salih, Ammar T., et al. "Single-material multilayer ZnS as anti-reflective coating for solar cell applications." Optics Communications 388 (2017): 84-89.
- [20].Gbashi, Kadhim R., et al. "Structural, morphology and optical properties of CZO thin films deposited by sol-gel spin coating for optoelectronic applications." Journal of Materials Science: Materials in Electronics 28.20 (2017): 15089-15094.
- [21].Najim, Aus A., et al. "Structural, topography, and optical properties of Ba-doped Mn3O4 thin films for ammonia gas sensing application." physica status solidi (a) 215.24 (2018): 1800379.
- [22]. Liu, Kun, et al. "Impact of aluminum doping on nonlinear absorption and ultrafast carriers dynamics of Al:CdO thin films." Optics & Laser Technology 157 (2023): 108675.